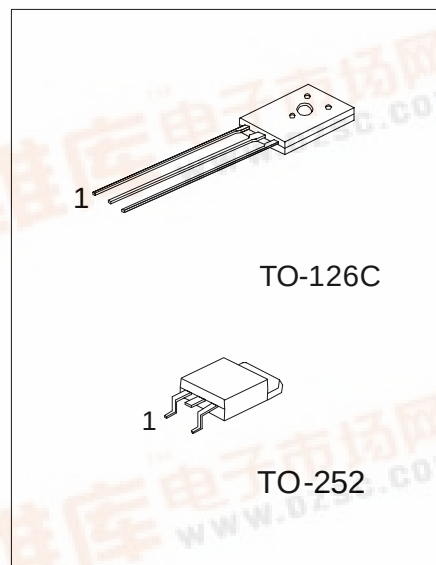



UNISONIC TECHNOLOGIES CO., LTD
2SB857
PNP SILICON TRANSISTOR
SILICON PNP TRANSISTOR
DESCRIPTION

Low frequency power amplifier.



*Pb-free plating product number: 2SB857L

ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2SB857-x-T6C-K	2SB857L-x-T6C-K	TO-126C	E	C	B	Bulk
2SB857-x-TN3-R	2SB857L-x-TN3-R	TO-252	B	C	E	Tape Reel
2SB857-x-TN3-T	2SB857L-x-TN3-T	TO-252	B	C	E	Tube

2SB857L-x-T6C-K 	(1)Packing Type	(1) K: Bulk, R: Tape Reel, T: Tube
	(2)Package Type	(2) T6C: TO-126C, TN3: TO-252
	(3)Rank	(3) x: refer to Classification of h_{FE2}
	(4)Lead Plating	(4) L: Lead Free Plating, Blank: Pb/Sn

2SB857

PNP SILICON TRANSISTOR

■ ABSOLUTE MAXIMUM RATING (Ta=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltages		V_{CBO}	-130	V
Collector-Emitter Voltage		V_{CEO}	-100	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current		I_C	-4	A
Collector Current (I_C Peak)		$I_{C(PEAK)}$	-8	A
Total Power Dissipation	TO-126C	P_D	1.5	W
	TO-252		1.9	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-40 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

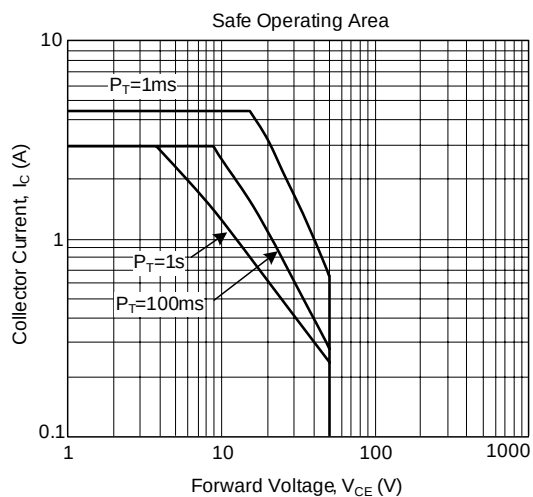
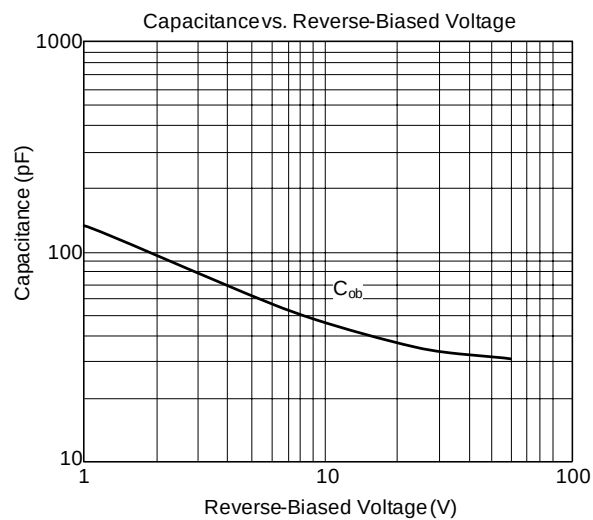
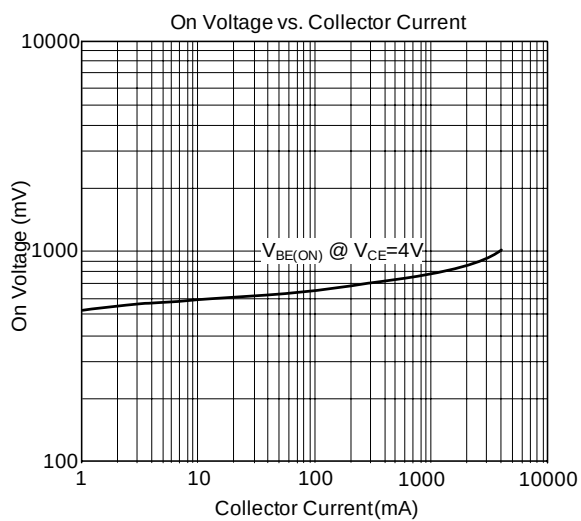
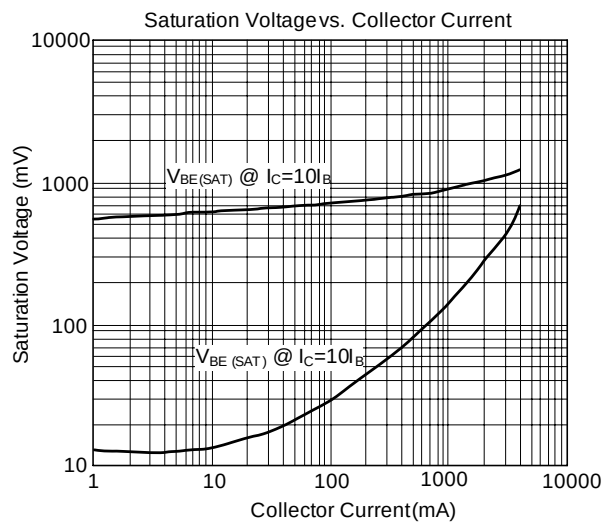
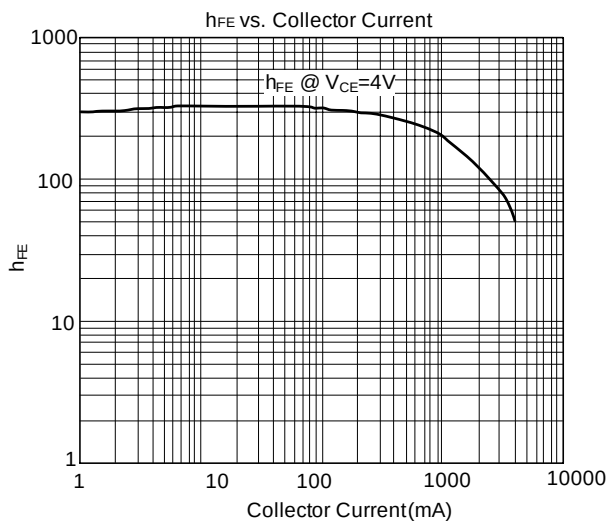
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -10\mu A, I_E = 0$	-130			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -50mA, I_B = 0$	-100			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Collector-Emitter Saturation Voltage	$*V_{CE(SAT)}$	$I_C = -2A, I_B = -0.2A$			-1	V
Base-Emitter Saturation Voltage	$*V_{BE(ON)}$	$V_{CE} = -4V, I_C = -1A$			-1	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -130V, I_C = 0$			-1	μA
DC Current Gain	$*h_{FE1}$	$V_{CE} = -4V, I_C = -0.1A$	35			
	$*h_{FE2}$	$V_{CE} = -4V, I_C = -1A$	60		320	
Transition Frequency	f_T	$V_{CE} = -4V, I_C = -500mA, f = 100MHz$		15		MHz

Note *Pulse Test: Pulse Width $\leq 380\mu S$, Duty Cycle $\leq 2\%$.

■ CLASSIFICATION OF h_{FE2}

CLASSIFICATION	B	C	D
RANGE	60 ~ 120	100 ~ 200	160 ~ 320

■ TYPICAL CHARACTERISTICS



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